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(21)Application number : 2000-049305 (71)Applicant : NIKON CORP

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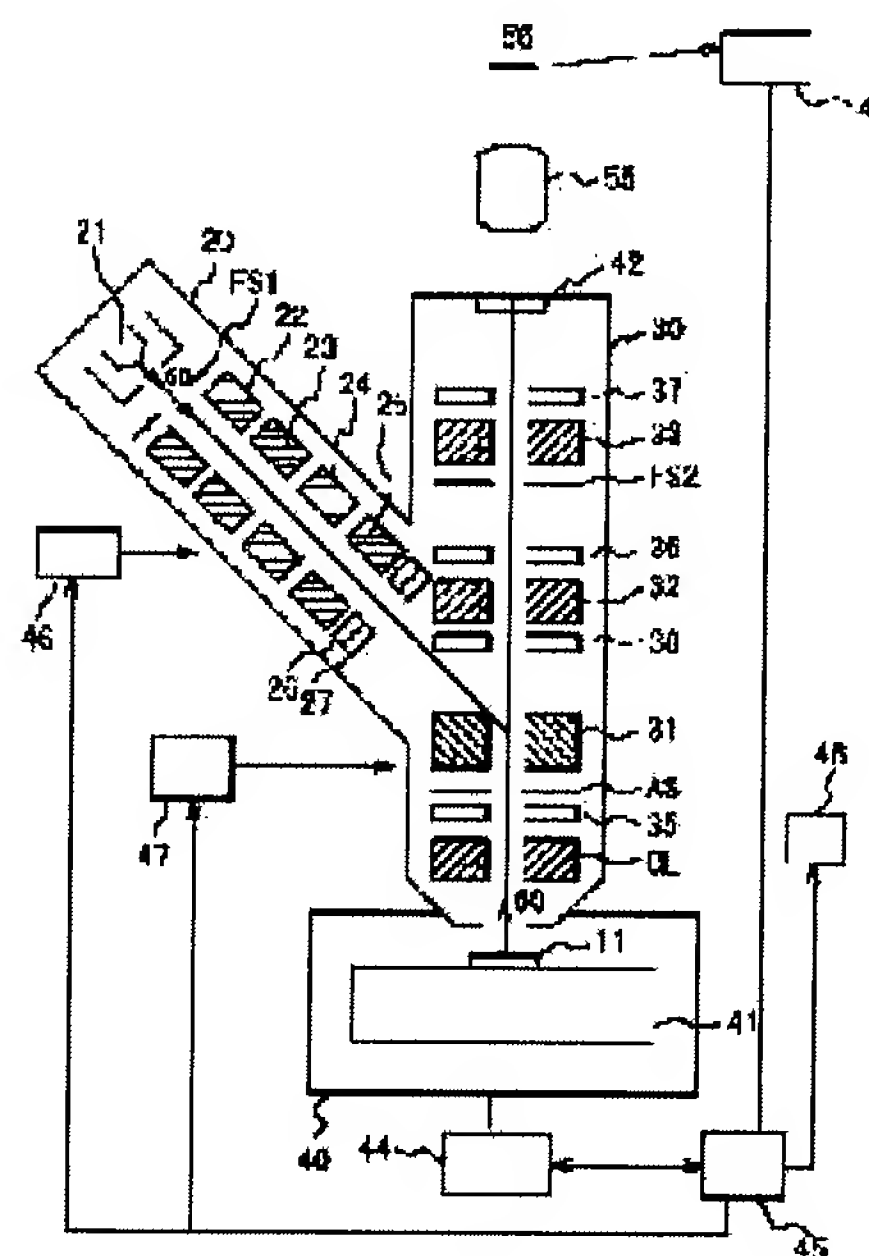
(54) CHARGED PARTICLE BEAM MICROSCOPE, FLAW INSPECTION DEVICE AND METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a charged particle beam microscope, capable of continuously changing the aspect ratio and the size of illumination visual field, a flaw inspection device and a method for manufacturing a semiconductor device.

SOLUTION: The charged particle beam microscope is equipped with an illumination optical system for illuminating the surface of a sample (material body surface) by the primary beam from a charged particle source via a primary optical system, having multi-electrode element lenses and a Wien filter ($E \times B$) and a mapping projection optical system (secondary optical system), forming electrons generated from the illuminated surface of the sample (material body

surface) into an image on an image surface, the multi-electrode element lenses of the primary optical system are arranged at least over four stages.



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